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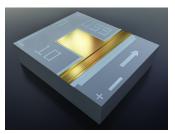


ML1000

1310 nm Fabry-Pérot Laser Diode for 1.25 Gb/s & 2.5 Gb/s

Overview

ML1000 is a laser chip with Modulight's highperformance RWG design. The excellent high temperature behaviour of the chip makes it suitable for low-cost uncooled short and intermediate reach applications in access and enterprise networks. The products are shipped as bare dies.



Applications

Communications

Gigabit Ethernet transceivers 1X/2X Fibre Channel SONET OC-48 SR SDH STM-I-16

Electro-optical Characteristics

| Parameter | Symbol | Min | Typical value | Max | Unit | Test condition* |
|---|--------------------------|------|------------------|------|------|--|
| Optical Output Power | P _{OPT} | 7 | - | - | mW | -40~85°C |
| Threshold Current | I _{TH} | - | 10 | 14 | mA | 25°C |
| | \mathbf{I}_{TH} | - | 21 | 28 | mA | 85°C |
| Operating Current | I _{OP} | - | 23 | 30 | mA | 25°C, P _{OPT} =5mW |
| | I _{OP} | - | 37 | 50 | mA | 85°C, P _{OPT} =5mW |
| Operating Voltage | V _{OP} | - | 1.1 | 1.5 | V | 25°C, P _{OPT} =5mW |
| Slope Efficiency | η | 0.3 | 0.38 | - | W/A | 25°C, P _{OPT} =5mW, 1-7 mW |
| | η | 0.22 | 0.29 | - | W/A | 85°C, P _{OPT} =5mW, 1-7 mW |
| Peak Wavelength | λ | 1290 | 1310 | 1330 | nm | 25°C, P _{OPT} =5mW |
| | λ | - | - | 1355 | nm | -40~85°C, P _{OPT} =5mW |
| Wavelength Temperature Coefficient | $\Delta\lambda/\Delta T$ | - | 0.46 | - | nm/K | -40~85°С, Р _{орт} =5mW |
| Spectral Width (FWHM)** | Δλ | - | 0.85 | 2 | nm | 25°C, P _{OPT} =5mW |
| Parallel Beam Divergence (FWHM) | θ | 15 | 21 | 30 | o | 25°C, P _{OPT} =5mW |
| Perpendicular Beam Divergence (FWHM) | θ⊥ | - | 38 | 45 | o | 25°C, P _{OPT} =5mW |
| Serial Resistance | R _s | - | 5.2 | - | Ω | 25°C, P _{OPT} =5mW, 1-7 mW |
| Modulation bandwidth *** | f _{-3dB} | 6 | - | - | GHz | 25°C, I _{OP} =I _{TH} +16mA |
| | f _{-3dB} | 4 | - | - | GHz | 25°C, I _{OP} =I _{TH} +16mA |



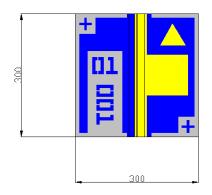
- * All temperatures refer to heatsink temperature ** -20 dB noise floor
- *** Chip-on carrier, ground-signal-ground microwave probe

Absolute Maximum Ratings

| Parameter | Symbol | Rating | Unit |
|-----------------------------|------------------|--------|------|
| Optical Output Power | P _{OPT} | 30 | mW |
| LD reverse voltage | V _{RLD} | 2 | V |
| LD forward current | I_{FLD} | 200 | mA |
| Operating temperature range | T _{OP} | -40~85 | °C |
| Storage temperature range | Ts | -40~85 | °C |

¹ A non-condensing environment is required for operation temperatures below 10 °C.

Mechanical Specification



All dimensions in microns Chip thickness 100 µm Polarity: p-contact (anode) up

Safety Information

- The laser light emitted from this laser diode is invisible and potentially harmful to the human eye. Avoid eye and skin exposure to the beam, both direct and reflected.
- Products are subject to the risks normally associated with sensitive electronic devices including static discharge, transients, and Please ensure ESD protection overload. prior to handling the products.
- These Modulight products are not intended use in systems where product for malfunction can reasonably be expected to result in personal injury.



Liability note

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